

Small Signal MOSFET 115 mAmps, 60 Volts N-Channel

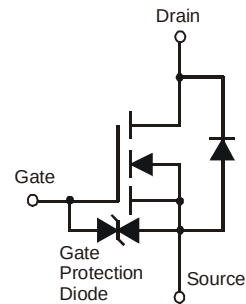
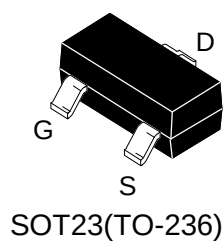
FEATURES:

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- ESD Protected : 1000V

APPLICATIONS:

- Load Switch

Circuit Diagram & Pin Configuration:



N-Channel

DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
2N7002-S03T	702	3000/Tape&Reel

MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	VDSS	60	Vdc
Drain-Gate Voltage (RGS = 1.0 MΩ)	VDGR	60	Vdc
Drain Current	ID		mAdc
– Continuous TC = 25°C		±115	
TC = 100°C		±75	
– Pulsed (Note 1)	IDM	±800	
Gate-Source Voltage	VGS	±20	Vdc
– Continuous			
– Non-repetitive (tp ≤ 50μs)	VGSM	±40	Vdc

THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation, FR-5 Board (Note 2) @ TA = 25°C	PD	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient(Note 2)	R θ JA	556	°C/W
Junction and Storage temperature	TJ,Tstg	-55~+150	°C

1. Pulse Test: Pulse Width $\leq$ 300 μ s, Duty Cycle $\leq$ 2.0%.
2. FR-5 = 1.0×0.75×0.062 in.

ELECTRICAL CHARACTERISTICS (Ta= 25°C)
OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = 10μAdc)	VBRDSS	60	-	-	Vdc
Zero Gate Voltage Drain Current TJ = 25°C (VGS = 0, VDS = 60 Vdc) TJ = 125°C	IDSS	-	-	1.0	μAdc
		-	-	500	
Gate–Body Leakage Current, Forward (VGS = 20 Vdc)	IGSSF	-	-	1.0	μAdc
Gate–Body Leakage Current, Reverse (VGS = - 20 Vdc)	IGSSR	-	-	-1.0	μAdc

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage (VDS = VGS, ID = 250μAdc)	VGS(th)	1.0	1.6	2.0	Vdc
On–State Drain Current (VDS ≥ 2.0 VDS(on), VGS = 10 Vdc)	ID(on)	500	-	-	mA
Static Drain–Source On–State Voltage (VGS = 10 Vdc, ID = 500 mAdc) (VGS = 5.0 Vdc, ID = 50 mAdc)	VDS(on)	-	-	3.75	Vdc
		-	-	0.375	
Static Drain–Source On–State Resistance (VGS = 10 Vdc, ID = 500 mAdc) TC = 25°C TC = 125°C (VGS = 5.0 Vdc, ID = 50 mAdc) TC = 25°C TC = 125°C	RDS(on)	-	1.4	7.5	Ohms
		-	-	13.5	
		-	1.8	7.5	
		-	-	13.5	
Forward Transconductance (VDS ≥ 2.0 VDS(on), ID = 200 mAdc)	gfs	80	-	-	mmhos

DYNAMIC CHARACTERISTICS

Input Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	Ciss	-	17	50	pF
Output Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	Coss	-	10	25	pF
Reverse Transfer Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	Crss	-	2.5	5.0	pF

SWITCHING CHARACTERISTICS

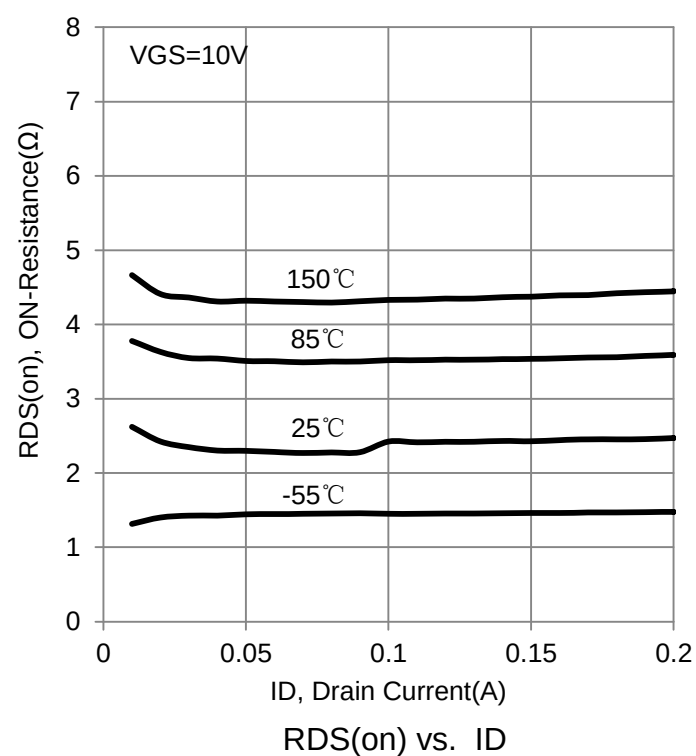
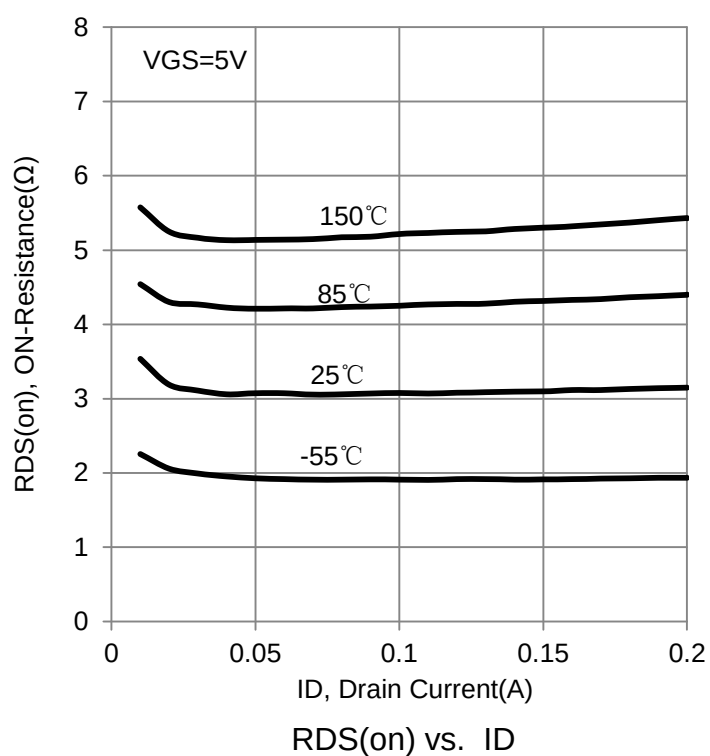
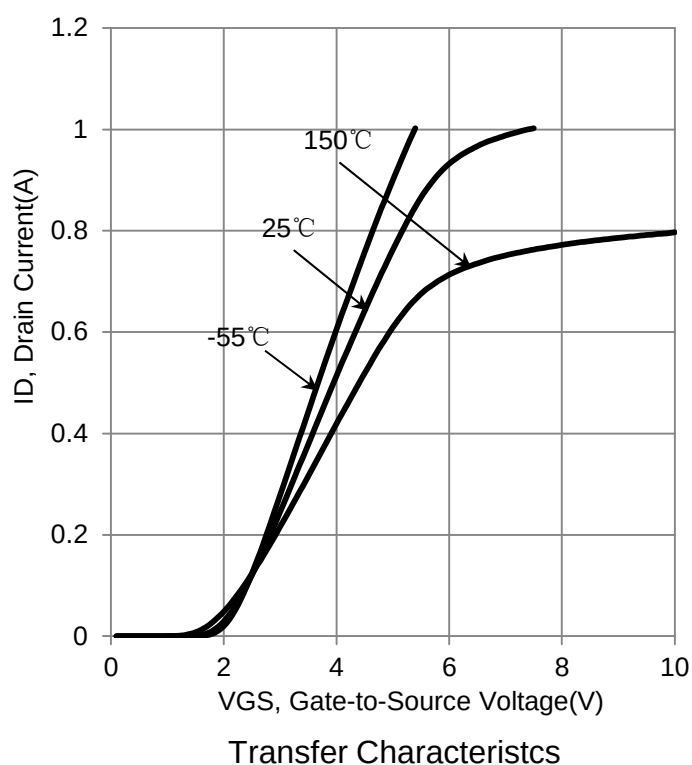
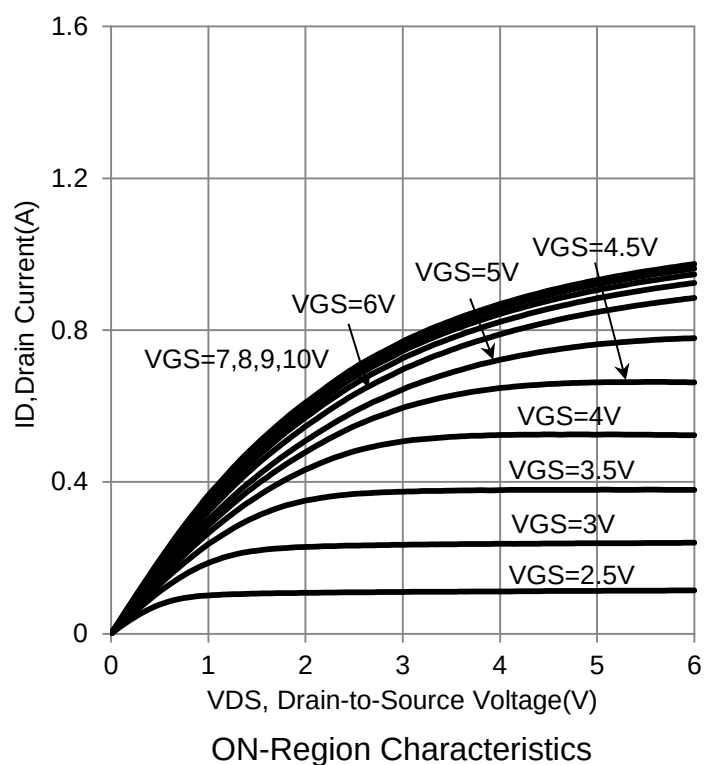
Turn-On Delay Time	(VDD = 25 Vdc, ID = 500 mAdc, RG = 25Ω, RL = 50 Ω, Vgen = 10 V)	td(on)	-	7	20	ns
Turn-Off Delay Time		td(off)	-	11	40	

BODY–DRAIN DIODE RATINGS

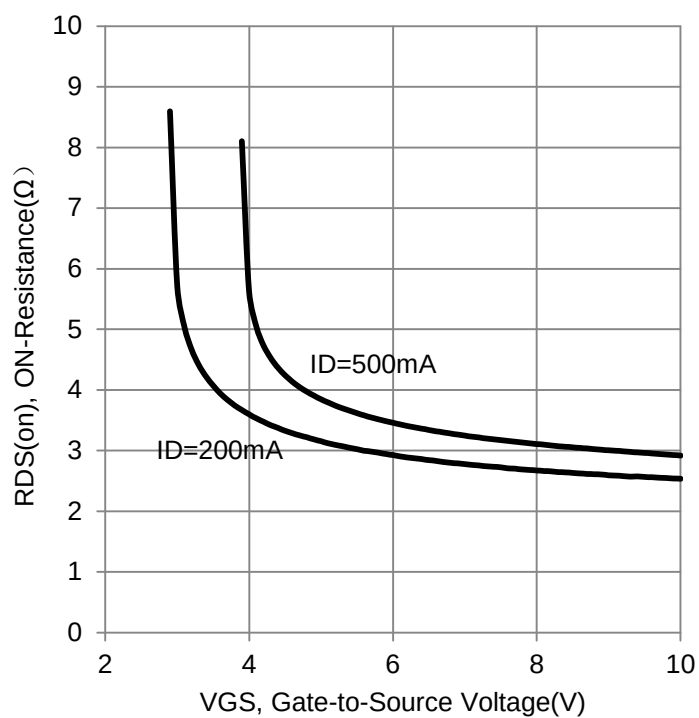
Diode Forward On–Voltage (IS = 115 mAdc, VGS = 0 V)	VSD	-	-	-1.5	Vdc
Source Current Continuous (Body Diode)	IS	-	-	-115	mAdc
Source Current Pulsed	ISM	-	-	-800	mAdc

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

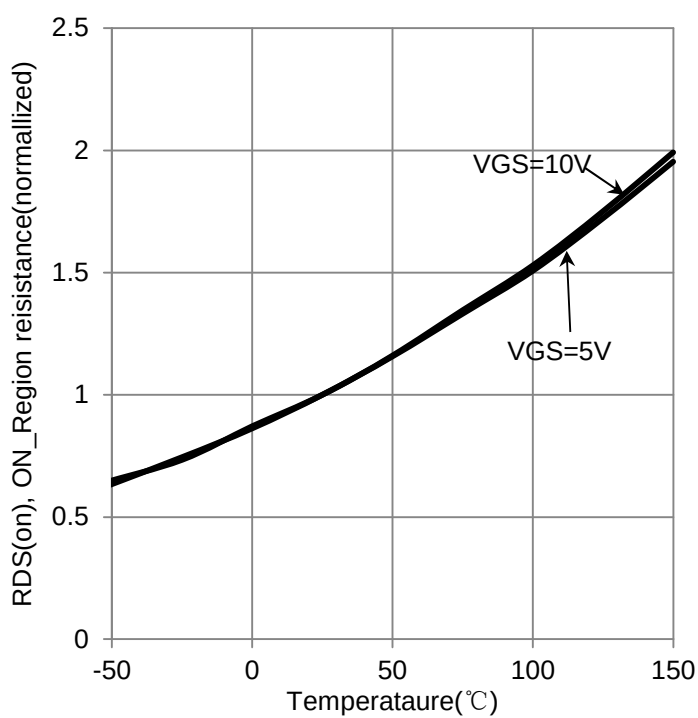
ELECTRICAL CHARACTERISTICS CURVES



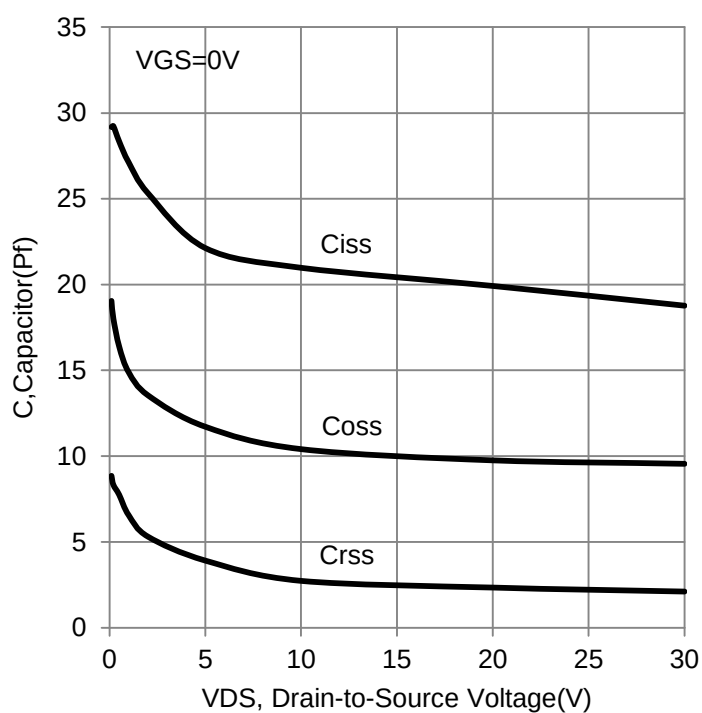
ELECTRICAL CHARACTERISTICS CURVES (Con.)



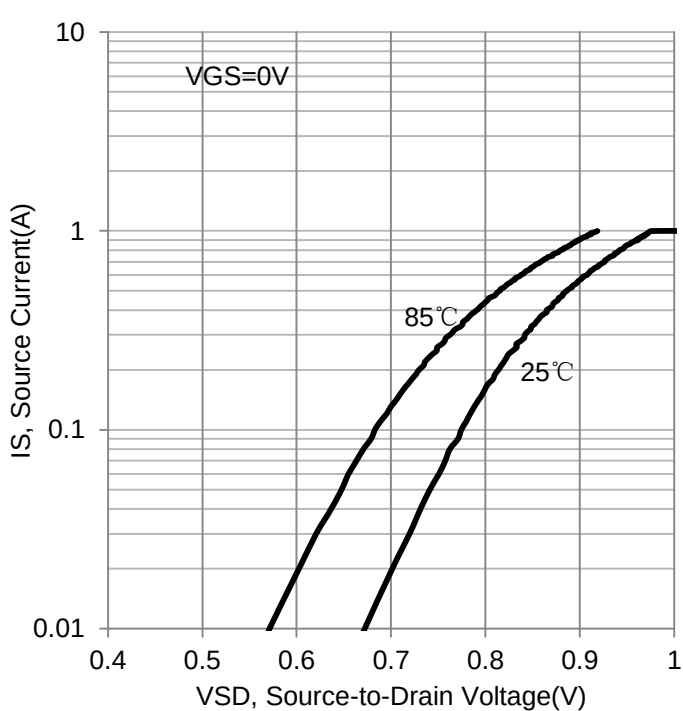
RDS(on) vs. VGS



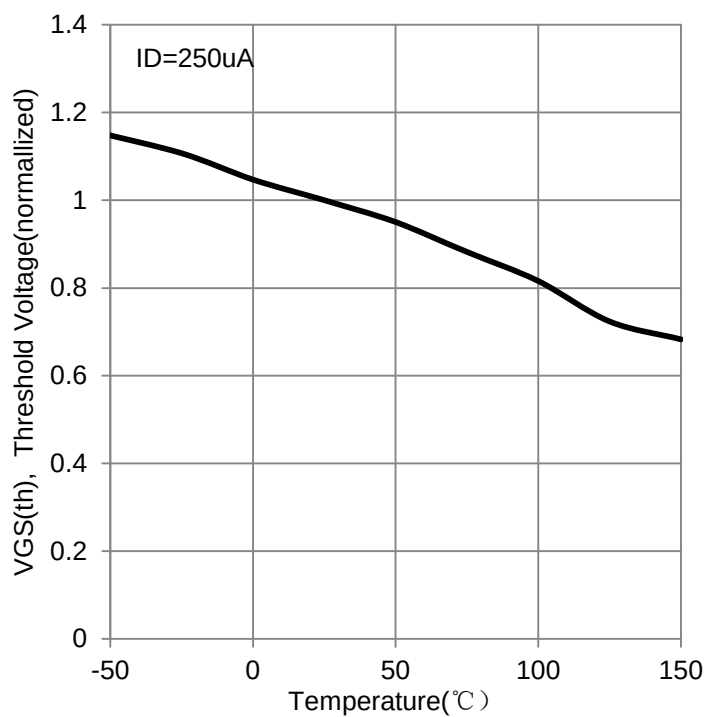
RDS(on) vs. Temperature



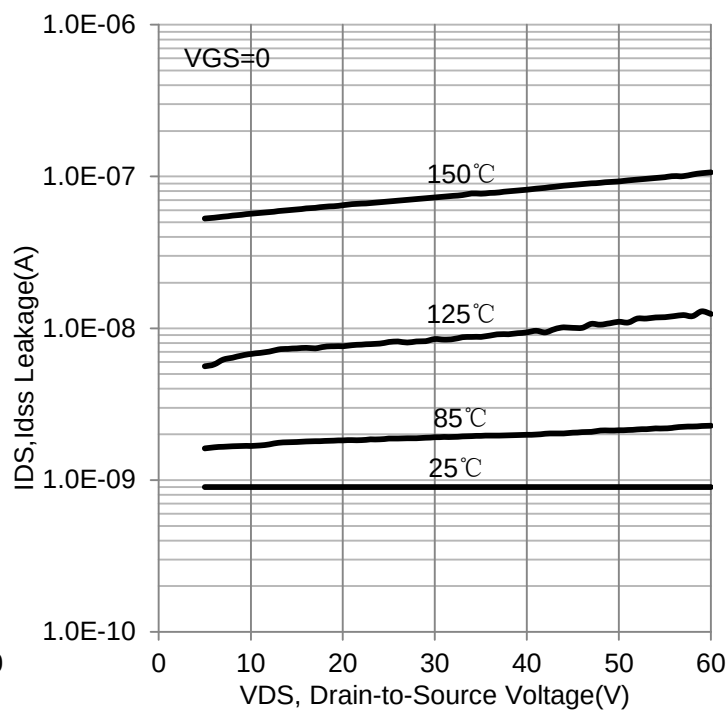
Capacitor vs. VDS



IS vs. VSD

ELECTRICAL CHARACTERISTICS CURVES (Con.)


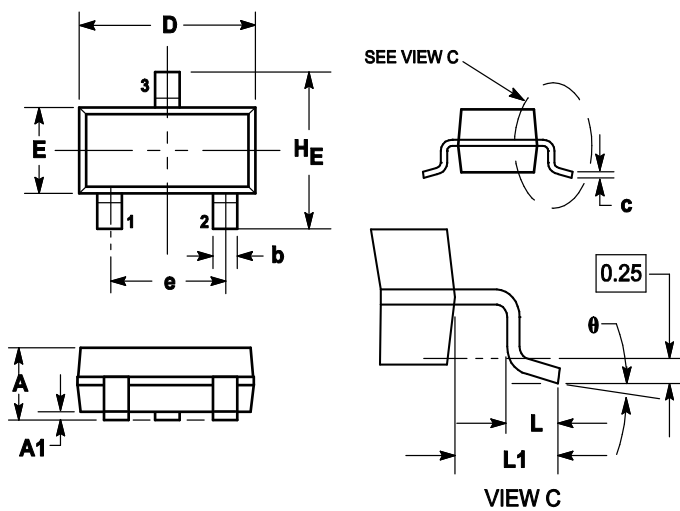
$V_{GS(th)}$ vs. Temperature



I_{DS} vs. V_{DS}

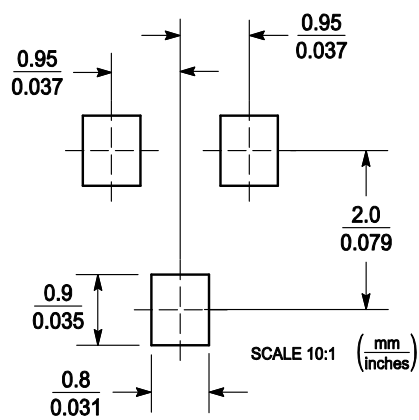
OUTLINE AND DIMENSIONS

- Notes:
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 - 2. CONTROLLING DIMENSION: MILLIMETERS.
 - 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
 - 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H _E	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

SOLDERING FOOTPRINT



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